

UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE
United States Patent and Trademark Office
Address: COMMISSIONER FOR PATENTS
P.O. Box 1450
Alexandria, Virginia 22313-1450
www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/631,921	07/31/2003	Jigish D. Trivedi	MICRON.104DV1	9664
20995	7590 03/03/2004		EXAM	INER
	MARTENS OLSON &	POMPEY, RON EVERETT		
	2040 MAIN STREET FOURTEENTH FLOOR			PAPER NUMBER
IRVINE, CA 92614			2812	
			DATE MAILED: 03/03/200	4

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)			
Office Autieus Communication	10/631,921	TRIVEDI, JIGISH D.			
Office Action Summary	Examiner	Art Unit			
	Ron E Pompey	2812			
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet with	the correspondence address			
A SHORTENED STATUTORY PERIOD FOR REPL' THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a repl If NO period for reply is specified above, the maximum statutory period or - Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a repl y within the statutory minimum of thirty (will apply and will expire SIX (6) MONTH e, cause the application to become ABAN	ly be timely filed 30) days will be considered timely. IS from the mailing date of this communication. NDONED (35 U.S.C. § 133).			
Status					
1) Responsive to communication(s) filed on	<u>_</u> .				
	s action is non-final.				
Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.					
Disposition of Claims					
4) ⊠ Claim(s) <u>1-25</u> is/are pending in the application 4a) Of the above claim(s) is/are withdra 5) □ Claim(s) is/are allowed. 6) ⊠ Claim(s) <u>1-25</u> is/are rejected. 7) □ Claim(s) is/are objected to. 8) □ Claim(s) are subject to restriction and/or	wn from consideration.				
Application Papers					
9) ☐ The specification is objected to by the Examiner. 10) ☐ The drawing(s) filed on is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.					
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).					
Replacement drawing sheet(s) including the correct					
Priority under 35 U.S.C. § 119					
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority application from the International Bureau * See the attached detailed Office action for a list	is have been received. Is have been received in App rity documents have been re u (PCT Rule 17.2(a)).	plication No eceived in this National Stage			
Attachment(s)					
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948)	4) Interview Sur	mmary (PTO-413) Mail Date			
 Notice of Dransperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 7-31-03. 		ormal Patent Application (PTO-152)			

Application/Control Number: 10/631,921 Page 2

Art Unit: 2812

DETAILED ACTION

Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 1-25 are rejected under 35 U.S.C. 103(a) as being unpatentable over Okumura (US 4,935,380) in further view of the admitted prior art and Yoo (US 5,605,854).

Okumura discloses the limitations of:

forming a gate stack on a substrate, the gate stack having at least one conductive layer (205, fig. 7A) and a source layer (213, fig. 7A) positioned on top of the at least one conductive layer, the source layer providing a source of transforming atoms (col. 6, ln. 59 – col. 7, ln. 9).

Okumura fails to disclose the limitations of:
exhuming a first layer of the gate stack so as to expose a portion of the source layer:

depositing a refractory material on the integrated circuit so that the refractory material contacts the exposed portion of the source layer of the gate stack and so that the refractory material is positioned on another device of the integrated circuit;

transforming the refractory material at the exposed portion of the source layer into a low resistance contact wherein the source layer provides transforming atoms to

source layer; and

Page 3

wherein annealing the refractory material comprises exposing the refractory material to a rapid thermal processing environment having an N2/NH3 ambient so as to increase the temperature of the refractory material to a value between 600 degrees Celsius and 750 degrees Celsius for a period of time between 10 seconds and 60 seconds.

a. However, the admitted prior art discloses:

exhuming (202, fig. 1) a first layer (216, fig. 1) of the gate stack so as to expose a portion of the source layer;

depositing a refractory material (218, fig. 1) on the integrated circuit so that the refractory material contacts the exposed portion of the source layer of the gate stack and so that the refractory material is positioned on another device of the integrated circuit; and

transforming the refractory material at the exposed portion of the source layer into a low resistance contact wherein the source layer provides transforming atoms to the portion of the refractory material positioned adjacent the exposed portion of the source layer (pg. 1, In. 28 – pg. 2, In. 28).

Therefore, it would have been obvious to one of ordinary skill in the art at the time of the invention to combine the admitted prior art with Okumura, because the first layer protects the gate structure from subsequent process and the refractory material provides an electrical connection between circuit nodes in an integrated circuit.

Application/Control Number: 10/631,921 Page 4

Art Unit: 2812

b. However, Yoo discloses:

wherein annealing the refractory material comprises exposing the refractory material to a rapid thermal processing environment having an N2/NH3 ambient so as to increase the temperature of the refractory material to a value between 600 degrees Celsius and 750 degrees Celsius for a period of time between 10 seconds and 60 seconds (col. 4, Ins. 43-67).

Therefore, it would have been obvious to one of ordinary skill in the art at the time of the invention to combine Yoo with Okumura and the admitted prior art, because rapid thermal processing has less effect on the doping concentrations set in the previous process due to less prolonged heat treatment.

EXAMINER'S AMENDMENT

4. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Mr. James Ausley on 2-18-04.

The application has been amended as follows:

In claim 25, line 6, replace ";" with --. --.

Art Unit: 2812

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Ron E Pompey whose telephone number is (571) 272-1680. The examiner can normally be reached on flex schedule.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, John Niebling can be reached on (571) 272-1679. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Ron Pompey

Art Unit: 2812

February 19, 2004

John F. Niebling

Supervisory Patent Examiner
Technology Center 2800